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UP04314G

Silicon NPN epitaxial planar type (Tr1)
 Silicon PNP epitaxial planar type (Tr2)

For switching/digital circuits

■ Features

- Two elements incorporated into one package (Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

■ Basic Part Number

- UNR2214 + UNR2114

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| | Parameter | Symbol | Rating | Unit |
|---------|---------------------------------------|-----------|-------------|------------------|
| Tr1 | Collector-base voltage (Emitter open) | V_{CBO} | 50 | V |
| | Collector-emitter voltage (Base open) | V_{CEO} | 50 | V |
| | Collector current | I_C | 100 | mA |
| Tr2 | Collector-base voltage (Emitter open) | V_{CBO} | -50 | V |
| | Collector-emitter voltage (Base open) | V_{CEO} | -50 | V |
| | Collector current | I_C | -100 | mA |
| Overall | Total power dissipation | P_T | 125 | mW |
| | Junction temperature | T_j | 125 | $^\circ\text{C}$ |
| | Storage temperature | T_{stg} | -55 to +125 | $^\circ\text{C}$ |

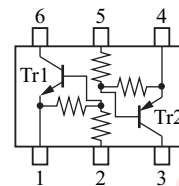
■ Package

- Code
SSMini6-F2
- Pin Name

| | |
|--------------------|--------------------|
| 1: Emitter (Tr1) | 4: Emitter (Tr2) |
| 2: Base (Tr1) | 5: Base (Tr2) |
| 3: Collector (Tr2) | 6: Collector (Tr1) |

■ Marking Symbol: CA

■ Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

- Tr1

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--|---------------|--|------|------|------|------------------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_C = 10 \mu\text{A}, I_E = 0$ | 50 | | | V |
| Collector-emitter voltage (Base open) | V_{CEO} | $I_C = 2 \text{ mA}, I_B = 0$ | 50 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = 50 \text{ V}, I_E = 0$ | | | 0.1 | μA |
| Collector-emitter cutoff current (Base open) | I_{CEO} | $V_{CE} = 50 \text{ V}, I_B = 0$ | | | 0.5 | μA |
| Emitter-base cutoff current (Collector open) | I_{EBO} | $V_{EB} = 6 \text{ V}, I_C = 0$ | | | 0.2 | mA |
| Forward current transfer ratio | h_{FE} | $V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$ | 80 | | | — |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA}$ | | | 0.25 | V |
| Output voltage high-level | V_{OH} | $V_{CC} = 5 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1 \text{ k}\Omega$ | 4.9 | | | V |
| Output voltage low-level | V_{OL} | $V_{CC} = 5 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1 \text{ k}\Omega$ | | | 0.2 | V |
| Input resistance | R_1 | | -30% | 10 | +30% | $\text{k}\Omega$ |
| Resistance ratio | R_1 / R_2 | | 0.17 | 0.21 | 0.25 | — |
| Transition frequency | f_T | $V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$ | | 150 | | MHz |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

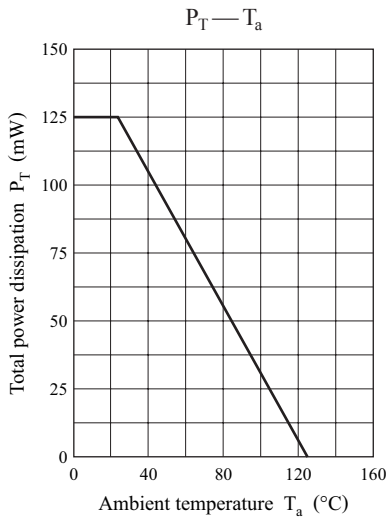
■ Electrical Characteristics (Continued) $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

• Tr2

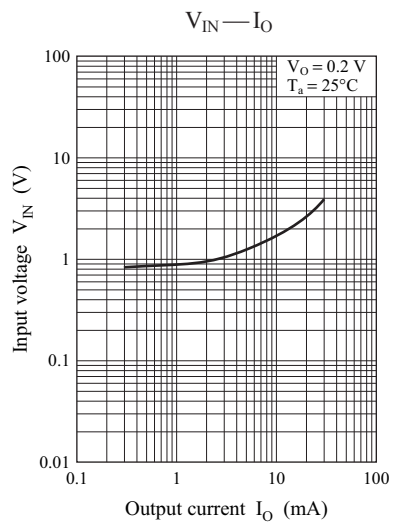
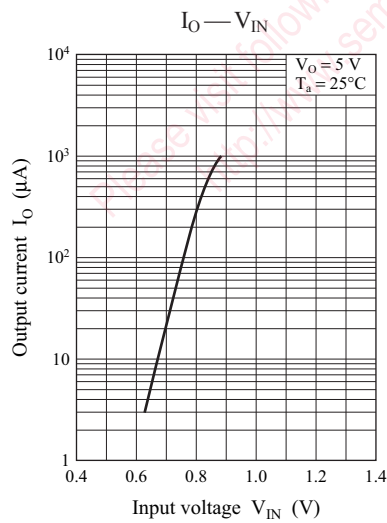
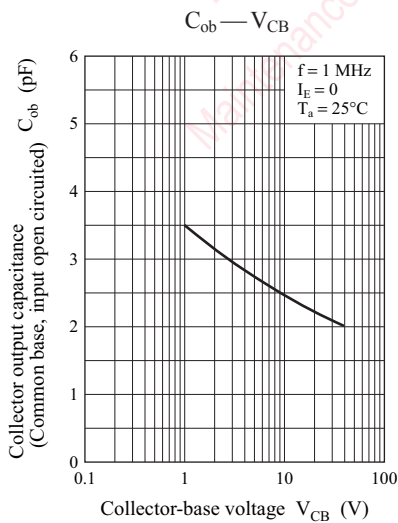
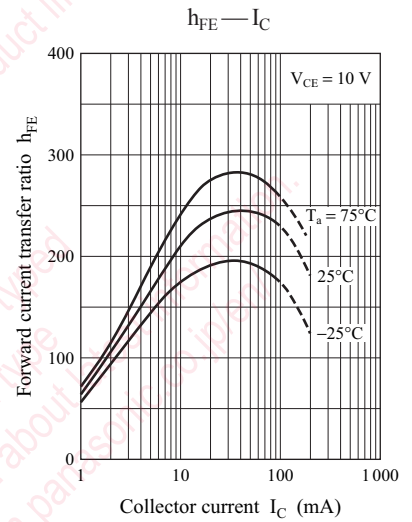
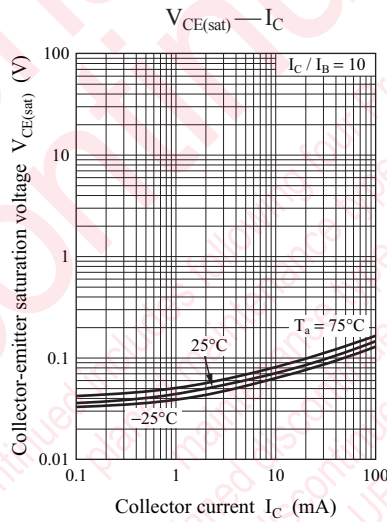
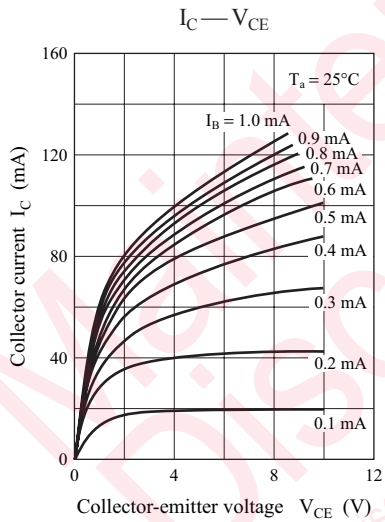
| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--|-------------------------------|--|------|------|-------|------------------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_{\text{C}} = -10 \mu\text{A}, I_{\text{E}} = 0$ | -50 | | | V |
| Collector-emitter voltage (Base open) | V_{CEO} | $I_{\text{C}} = -2 \text{mA}, I_{\text{B}} = 0$ | -50 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{\text{CB}} = -50 \text{V}, I_{\text{E}} = 0$ | | | -0.1 | μA |
| Collector-emitter cutoff current (Base open) | I_{CEO} | $V_{\text{CE}} = -50 \text{V}, I_{\text{B}} = 0$ | | | -0.5 | μA |
| Emitter-base cutoff current (Collector open) | I_{EBO} | $V_{\text{EB}} = -6 \text{V}, I_{\text{C}} = 0$ | | | -0.2 | mA |
| Forward current transfer ratio | h_{FE} | $V_{\text{CE}} = -10 \text{V}, I_{\text{C}} = -5 \text{mA}$ | 80 | | | — |
| Collector-emitter saturation voltage | $V_{\text{CE(sat)}}$ | $I_{\text{C}} = -10 \text{mA}, I_{\text{B}} = -0.3 \text{mA}$ | | | -0.25 | V |
| Output voltage high-level | V_{OH} | $V_{\text{CC}} = -5 \text{V}, V_{\text{B}} = -0.5 \text{V}, R_{\text{L}} = 1 \text{k}\Omega$ | -4.9 | | | V |
| Output voltage low-level | V_{OL} | $V_{\text{CC}} = -5 \text{V}, V_{\text{B}} = -2.5 \text{V}, R_{\text{L}} = 1 \text{k}\Omega$ | | | -0.2 | V |
| Input resistance | R_{I} | | -30% | 10 | +30% | $\text{k}\Omega$ |
| Resistance ratio | $R_{\text{I}} / R_{\text{2}}$ | | 0.17 | 0.21 | 0.25 | — |
| Transition frequency | f_{T} | $V_{\text{CB}} = -10 \text{V}, I_{\text{E}} = 1 \text{mA}, f = 200 \text{MHz}$ | | 80 | | MHz |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

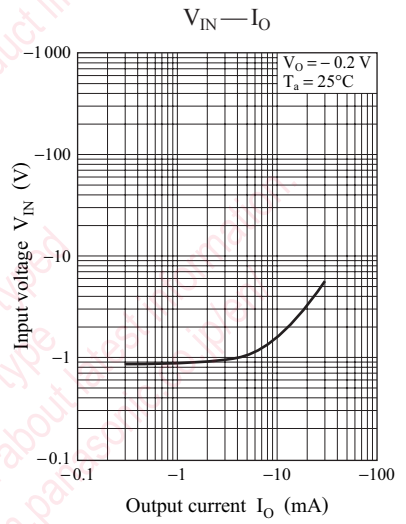
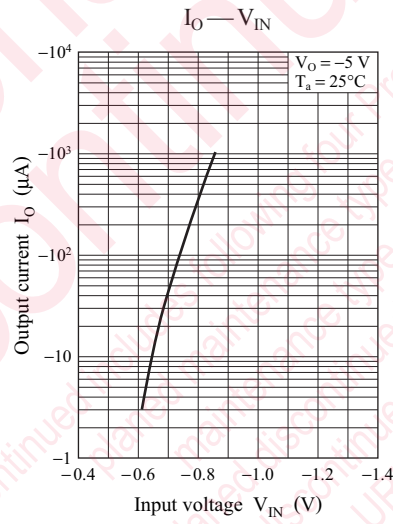
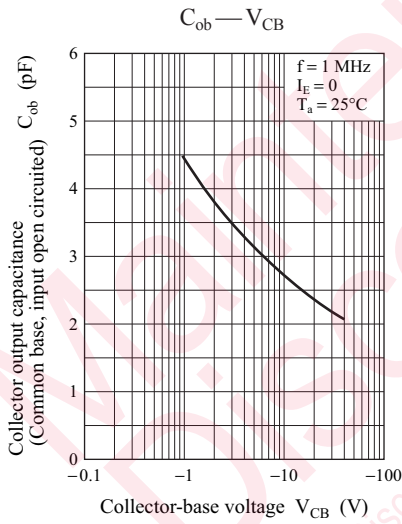
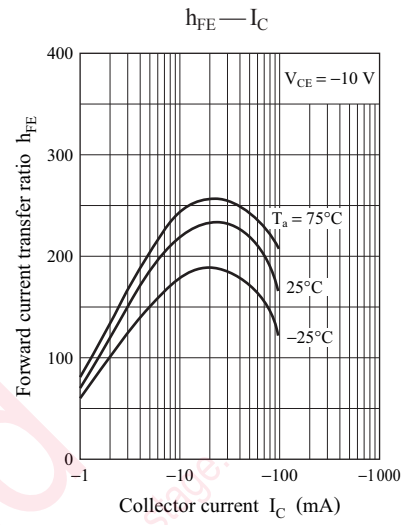
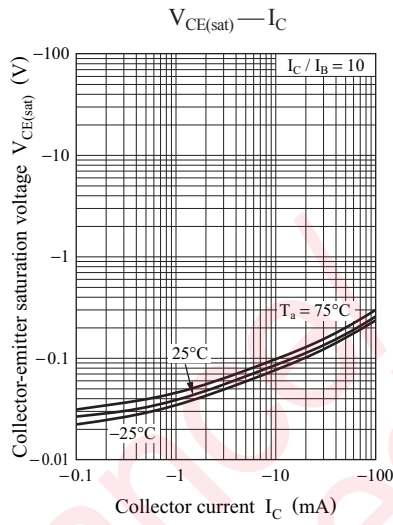
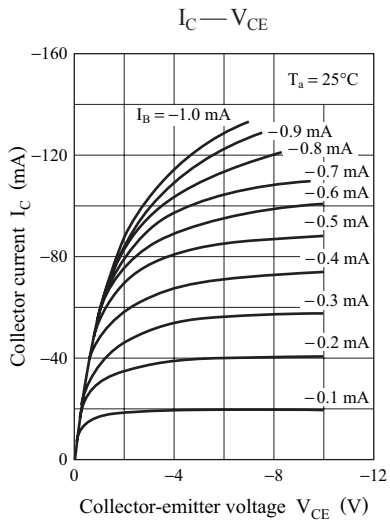
Common characteristics chart



Characteristics charts of Tr1

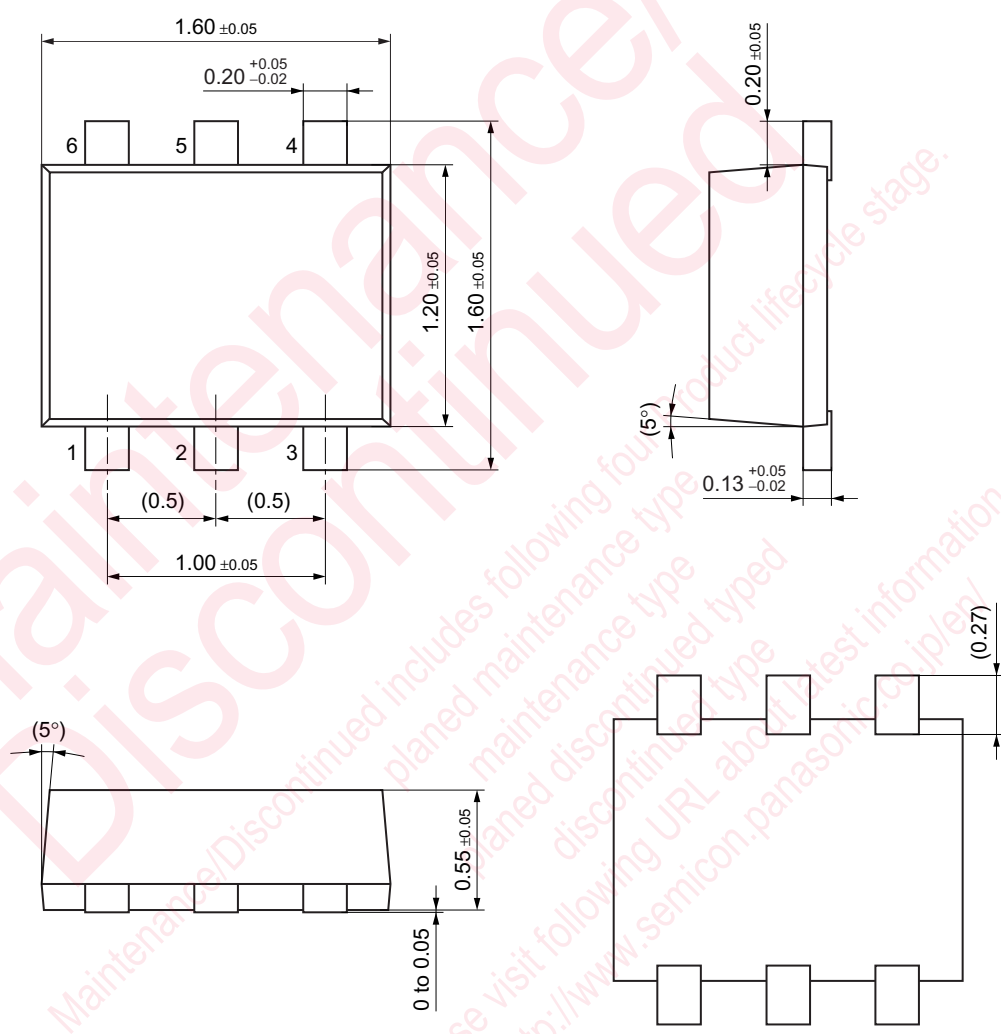


Characteristics charts of Tr2



SSMini6-F2

Unit: mm



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